



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:

SHI-QING WANG, ET AL

Docket: 30-4687 (4780)

Serial Number: 09/328,646

Group Art Unit: 2811

Filed: June 9, 1999

Examiner: H. Vu

For: INTEGRATED CIRCUITS WITH MULTIPLE LOW DIELECTRIC-CONSTANT
INTER- METAL DIELECTRICS

#719
12/6/00

AMENDMENT

Assistant Commissioner for Patents
Washington, DC 20231

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Sir:

In response to the Office Action mailed October 3, 2000 applicant makes the following
election in response to the restriction requirement.

In the claims:

EI
7. (Amended) [A process for producing an] An integrated circuit structure produced by a
process which comprises

- (a) providing a substrate which comprises a pattern of metal lines on the substrate and a
dielectric on the substrate between the metal lines;
- (b) depositing an organic dielectric layer on the substrate;
- (c) depositing an inorganic dielectric layer on the organic dielectric;
- (d) etching a pattern of vias through the inorganic dielectric layer;
- (e) etching a pattern of vias through the organic dielectric layer which correspond to the
pattern of vias through the inorganic dielectric layer;
- (f) applying a photoresist to the top of the inorganic dielectric layer and filling the vias in
the organic dielectric layer and the inorganic dielectric layer with photoresist;